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## **Dual N-Channel 30 V (D-S) MOSFET**

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
30	10 at V <sub>GS</sub> = 10 V	35	18 nC			
30	15.5 at V <sub>GS</sub> = 4.5 V	35				

#### **FEATURES**

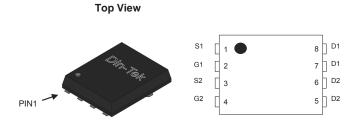
- DT-Trench Power MOSFET
- 100 %  $R_q$  and UIS Tested
- Green Device Available
- · Fast Switching Speed

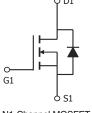
## RoHS

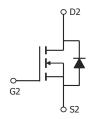
#### **APPLICATIONS**

- Battery Protection
- · Load Switch

#### **DFN5X6-8L-Dual Pin Configuration**







N1-Channel MOSFET

N2-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	30	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Proin Current /T = 150 °C)3	T <sub>C</sub> = 25 °C	,	35	А	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	- I <sub>D</sub>	26.5		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	140			
Single Avalanche Energy	E <sub>AS</sub>	68	mJ		
Maximum Bower Dissinations	T <sub>C</sub> = 25 °C	В	43	W	
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	P <sub>D</sub>	17		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub> 62		°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	2.9	- 10/00		

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c.  $\,$  Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>8JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	-	2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	-	-	1	<u>μ</u> Α	
Zero Gate Voltage Drain Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	100		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	35	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	D ·	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	10	13.5		
Diain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A	-	15.5	21	mΩ	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 10 A	-	42	-	S	
Dynamic <sup>b</sup>				•			
Input Capacitance	C <sub>iss</sub>		-	850	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	80	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	9	-		
Total Gate Charge <sup>c</sup>	Qg		-	18	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	4.5	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	5.8	-		
Gate Resistance	$R_g$	f = 1 MHz	-	1.8	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	6.5	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, I_D = 10 \text{ A}, R_g = 3 \Omega$	-	10	-		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	22	-	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	7	-		
Drain-Source Body Diode Ratings and	Characterist	ics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	35	Α	
Pulsed Current	I <sub>SM</sub>		-	-	140	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	1 - 10 A di/dt = 100 A/vc	-	18	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt } = 100 \text{ A/}\mu\text{s}$	-	20	-	nC	

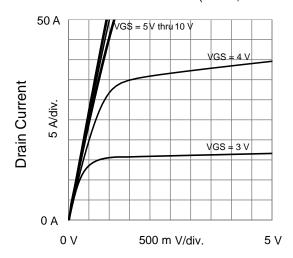
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

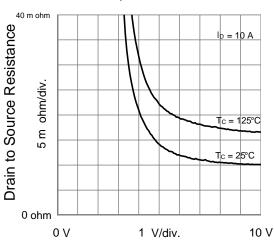
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



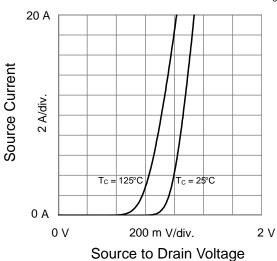
#### TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



Drain to Source Voltage Output Characteristics

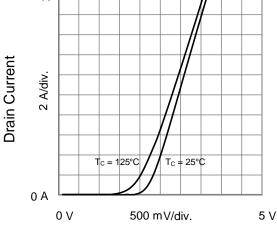


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

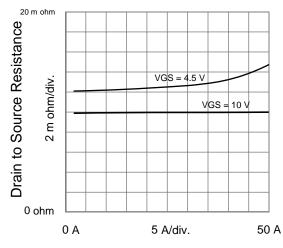


**Body Diode Forward Characteristics** 

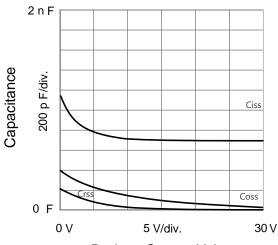
20 A



Gate to Source Voltage Transfer Characteristics



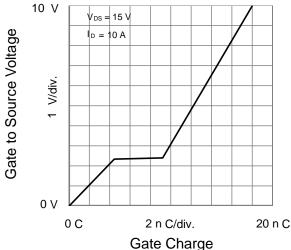
**Drain Current** 



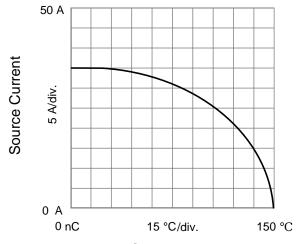
Drain to Source Voltage Capacitances



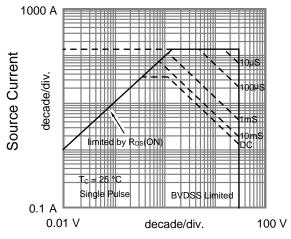
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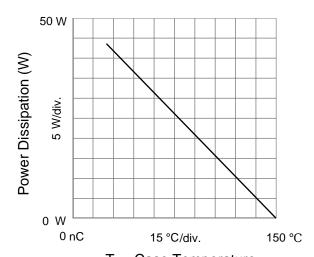
Gate to Source Voltage vs. GateCharge



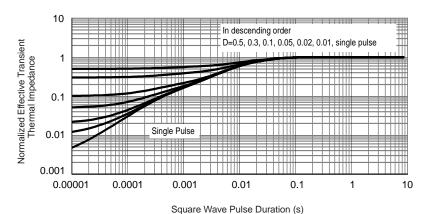
T<sub>C</sub> - Case Temperature



Source to Drain Voltage
Safe Operating Area, Junction-to-Case



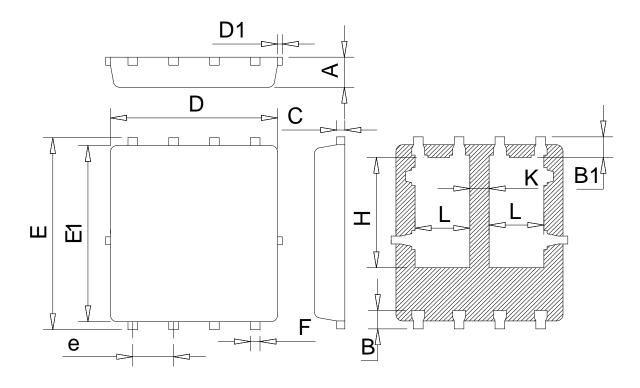
T<sub>C</sub> - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



## **DFN5X6-8L-D PACKAGE OUTLINE**



# COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
А	0.85	0.95	1.05
В	0.46	0.58	0.73
B1	0.52	0.65	0.78
С	0.18	0.254	0.32
D	4.70	5.20	5.50
D1	-	-	0.18
Е	5.75	6.05	6.35
E1	5.35	5.65	5.85
е	1.15	1.27	1.50
F	0.15	0.30	0.50
Н	3.15	3.47	3.80
L	1.35	1.70	2.10
K	0.35	0.60	1.00





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